COMPOSITION FOR PHOTORESIST STRIPPING SOLUTION AND PROCESS OF PHOTORESIST STRIPPING

Abstract

The present invention provides a composition for photoresist stripping solution which shows a superior stripping property of photoresists and damaged photoresist layers remained after dry etching in the fabrication process of semiconductor circuit devices, without attacking new wiring materials and interlayer insulating film materials, as well as a process of stripping of photoresists and damaged photoresist layers. The composition for photoresist stripping solution which contains at least one of acetylene alcohol compounds and organic sulfonic acid compounds, and at least one of polyvalent alcohols and their derivatives is used.